

What Is Claimed Is:

1. A method of producing a micromechanical sensor arrangement, comprising the steps of:
 - providing a wafer having a surface and edge areas;
 - dividing the surface of the wafer into positive areas, to be subsequently etched in a wet chemical etching process, and negative areas including the edge areas of the wafer;
 - providing the negative areas with a passivation layer to protect the negative areas from the subsequent wet chemical etching process;
 - etching the wafer in the wet chemical etching process; and
 - removing the passivation layer.
2. The method according to claim 1, wherein the dividing step includes the sub-steps of:
 - applying a nitride layer; and
 - structuring the nitride layer using a photoresist technique so that the positive areas are defined by a part of the surface covered with the nitride layer.
3. The method according to claim 2, further comprising the step of removing the nitride layer at least in subareas of the positive areas, after the negative areas are provided and before the wafer is etched.
4. The method according to claim 3, further comprising the steps of:
 - applying a thin further passivation layer in the subareas, after the removal of the nitride layer in the subareas and before the wafer is etched; and
 - completely removing the nitride layer.
5. The method according to claim 2, wherein the photoresist technique is an integrated circuit photoresist technique.
6. The method according to claim 2 wherein the structuring step includes

Subarea

the step of removing a photoresist at an edge after exposing the photoresist.

7. The method according to claim 6, wherein the photoresist is removed after exposing and developing the photoresist.

8. The method according to claim 1, wherein the passivation layer is an oxide layer.

9. The method according to claim 8, further comprising the step of applying the oxide layer in a LOCOS process.

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